

Data Sheet August 3, 2007 FN6293.3

# Micropower, Single Supply, Rail-to-Rail Input-Output Instrumentation Amplifiers

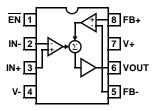
The EL8171 and EL8172 are micropower instrumentation amplifiers optimized for single supply operation over the +2.4V to +5.5V range. Inputs and outputs can operate rail-to-rail. As with all instrumentation amplifiers, a pair of inputs provide very high common-mode rejection and are completely independent from a pair of feedback terminals. The feedback terminals allow zero input to be translated to any output offset, including ground. A feedback divider controls the overall gain of the amplifier.

The EL8172 is compensated for a gain of 100 or more, and the EL8171 is compensated for a gain of 10 or more. The EL8171 and EL8172 have PMOS input devices that provide sub-nA input bias currents.

The amplifiers can be operated from one lithium cell or two Ni-Cd batteries. The EL8171 and EL8172 input range goes from below ground to slightly above positive rail. The output stage swings completely to ground (ground sensing) or positive supply - no pull-up or pull-down resistors are needed.

### **Pinout**

**EL8171, EL8172 (8 LD SOIC)** TOP VIEW



### **Features**

- 95µA maximum supply current
- · Maximum input offset voltage
  - 300µV (EL8172)
  - 1500µV (EL8171)
- · 50pA maximum input bias current
- 450kHz -3dB bandwidth (G = 10)
- 170kHz -3dB bandwidth (G = 100)
- · Single supply operation
  - Input voltage range is rail-to-rail
  - Output swings rail-to-rail
  - Ground Sensing
- Pb-free plus anneal available (RoHS compliant)

# **Applications**

- · Battery- or solar-powered systems
- · Strain gauges
- · Current monitors
- Thermocouple amplifiers

# **Ordering Information**

PART NUMBER (Note)	PART MARKING	PACKAGE (Pb-free)	PKG. DWG. #	
EL8171FSZ*	8171FSZ	8 Ld SOIC	MDP0027	
EL8172FSZ*	8172FSZ	8 Ld SOIC	MDP0027	

<sup>\*</sup>Add "-T7" suffix for tape and reel. Please refer to TB347 for details on reel specifications.

NOTE: Intersil Pb-free plus anneal products employ special Pb-free material sets; molding compounds/die attach materials and 100% matte tin plate termination finish, which are RoHS compliant and compatible with both SnPb and Pb-free soldering operations. Intersil Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.

# **Absolute Maximum Ratings** $(T_A = +25^{\circ}C)$

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# **Thermal Information**

Thermal Resistance	$\theta_{JA}$ (°C/W)
8 Ld SOIC Package	110
Output Short-Circuit Duration	Indefinite
Ambient Operating Temperature	°C to +125°C
Storage Temperature	°C to +150°C
Pb-free reflow profile	ee link below
http://www.intersil.com/pbfree/Pb-FreeReflow.asp	

CAUTION: Do not operate at or near the maximum ratings listed for extended periods of time. Exposure to such conditions may adversely impact product reliability and result in failures not covered by warranty.

IMPORTANT NOTE: All parameters having Min/Max specifications are guaranteed. Typical values are for information purposes only. Unless otherwise noted, all tests are at the specified temperature and are pulsed tests, therefore:  $T_J = T_C = T_A$ 

# **Electrical Specifications**

 $V_+ = +5V$ ,  $V_- = GND$ ,  $VCM = 1/2V_+$   $V_{EN} = V_-$ ,  $R_L = Open$ ,  $T_A = +25^{\circ}C$ , unless otherwise specified. **Boldface limits apply over the operating temperature range**, -40°C to +125°C.

PARAMETER	DESCRIPTION	CONDITIONS	MIN (Note 1)	TYP	MAX (Note 1)	UNIT
DC SPECIFICA	TIONS					
Vos	Input Offset Voltage	EL8171	-1.5 <b>-2</b>	±0.47	1.5 <b>2</b>	mV
		EL8172	-0.3 - <b>0.7</b>	±0.07	0.3 <b>0.7</b>	mV
TCV <sub>OS</sub>	Input Offset Voltage Temperature	EL8171		1.5		μV/°C
	Coefficient	EL8172		0.14		μV/°C
los	Input Offset Current, ± IN, ± FB		-25 <b>-500</b>	±4	25 <b>500</b>	pA pA
l <sub>Β</sub>	Input Bias Current		-50 <b>-4</b>	±10	50 <b>4</b>	pA nA
$V_{IN}$	Input Voltage Range	Guaranteed by CMRR test	0		5	V
CMRR	Common Mode Rejection Ratio	V <sub>CM</sub> = 0V to +5V	75	100		dB
PSRR	Power Supply Rejection Ratio	EL8171, V <sub>+</sub> = 2.4V to 5V	75	90		dB
		EL8172, $V_{+} = 2.4V$ to 5V	75	100		dB
E <sub>G</sub>	Gain Error	EL8171, $R_L = 100$ kΩ to 2.5V	-0.7	±0.15	0.7	%
		EL8172, $R_L = 100k\Omega$ to 2.5V	-1 <b>-1.5</b>	±0.2	+1 1.5	% %
V <sub>OUT</sub>	Maximum Voltage Swing	Output low, $100k\Omega$ to $2.5V$		4	10 <b>10</b>	mV mV
		Output low, $1k\Omega$ to $2.5V$		0.13	0.2 <b>0.25</b>	V V
		Output high, $100k\Omega$ to $2.5V$	4.985 <b>4.980</b>	4.996		V V
		Output high, $1k\Omega$ to GND	4.860 <b>4.750</b>	4.87		V V
I <sub>S,EN</sub>	Supply Current, Enabled		45 <b>38</b>	65	95 <b>110</b>	μΑ
I <sub>S,DIS</sub>	Supply Current, Disabled	EL8171: <del>EN</del> = V <sub>+</sub>	1.8 <b>1.3</b>	2.6	4 5	μA
		EL8172: <del>EN</del> = V <sub>+</sub>	1.8 <b>1.5</b>	4.5	7.0 <b>25</b>	μA

# Electrical Specifications $V_+ = +5V$ , $V_- = GND$ , $VCM = 1/2V_+$ $V_{EN} = V_-$ , $R_L = Open$ , $T_A = +25^{\circ}C$ , unless otherwise specified. Boldface limits apply over the operating temperature range, -40°C to +125°C. (Continued)

PARAMETER	DESCRIPTION		CONDITIONS	MIN (Note 1)	TYP	MAX (Note 1)	UNIT
V <sub>ENH</sub>	EN Pin for Shut-down			2			V
I <sub>ENH</sub>	EN Pin for Shut-down				0.5		μA
V <sub>ENL</sub>	EN Pin for Power-on					0.8	V
I <sub>ENL</sub>	EN Pin for Power-on				0.5		μA
V <sub>SUPPLY</sub>	Supply Operating Range	V+ to V- (N	ote 2)	2.4		5.5	٧
I <sub>O+</sub>	Output Source Current into $10\Omega$ to $V_{+}/2$	V <sub>+</sub> = 5V		23 <b>19</b>	32		mA
		V <sub>+</sub> = 2.4V		6 <b>4.5</b>	8		mA
I <sub>O</sub> -	Output Sink Current into 10Ω to V <sub>+</sub> /2	V <sub>+</sub> = 5V		19 <b>15</b>	26		mA
		V <sub>+</sub> = 2.4V		5 <b>4</b>	7		mA
AC SPECIFICAT	TIONS			·	•	•	•
-3dB BW	-3dB Bandwidth	EL8171	Gain = 10V/V		450		kHz
			Gain = 20		210		kHz
			Gain = 50		66		kHz
			Gain = 100		33		kHz
		EL8172	Gain = 100		170		kHz
			Gain = 200		70		kHz
			Gain = 500		25		kHz
			Gain = 1000		12		kHz
e <sub>N</sub>	Input Noise Voltage	EL8171	f = 0.1Hz to 10Hz		14		μV <sub>P-P</sub>
		EL8172			10		μV <sub>P-P</sub>
	Input Noise Voltage Density	EL8171	f <sub>O</sub> = 1kHz		220		nV/√Hz
		EL8172			80		nV/√Hz
i <sub>N</sub>	Input Noise Current Density	EL8171, f <sub>o</sub> = 1kHz			0.9		pA/√Hz
		EL8172, f <sub>o</sub> = 1kHz			0.2		pA/√Hz
CMRR @ 60Hz	Input Common Mode Rejection Ratio	EL8171 $V_{CM} = 1V_{PP}$ , $R_L = 10kΩ$ to $V_{CM}$			85		dB
					100		dB
PSRR+ @	Power Supply Rejection Ratio (V <sub>+</sub> )	EL8171 V <sub>+</sub> , V <sub>-</sub> = ±2.5V, V <sub>SOURCE</sub> = 1V <sub>PP</sub> , R <sub>L</sub> = 10kΩ to V <sub>CM</sub>			90		dB
120Hz					92		dB
PSRR- @	Power Supply Rejection Ratio (V <sub>-</sub> )	EL8171 $V_+$ , $V$ = ±2.5V, $V_{SOURCE}$ = 1V <sub>PP</sub> , $R_L$ = 10kΩ to V <sub>CM</sub>			97		dB
120Hz					92		dB
TRANSIENT RE	SPONSE				ı	_	
SR	Slew Rate	$R_L = 1k\Omega$ to	GND	0.4 <b>0.35</b>	0.55	0.7 <b>0.7</b>	V/µs

### NOTES:

- 1. Parts are 100% tested at +25°C. Over temperature limits established by characterization and are not production tested.
- 2.  $V_{SUPPLY} = +5.25V$  max when  $V_{ENL} = +V$  (device in disable state).

# Typical Performance Curves V<sub>+</sub> = 5V, V<sub>-</sub> = 0V, V<sub>CM</sub> = 2.5V, V<sub>EN</sub> = V-, R<sub>L</sub> = Open, unless otherwise specified.

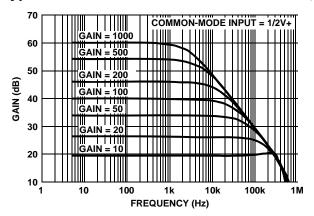


FIGURE 1. EL8171 FREQUENCY RESPONSE vs CLOSED LOOP GAIN

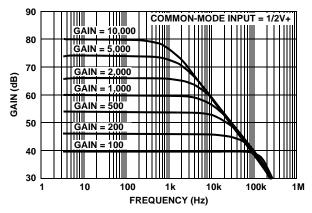


FIGURE 2. EL8172 FREQUENCY RESPONSE vs CLOSED LOOP GAIN

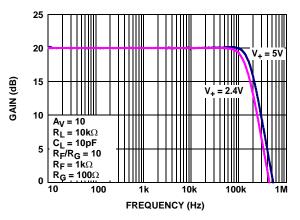


FIGURE 3. EL8171 FREQUENCY RESPONSE vs SUPPLY VOLTAGE

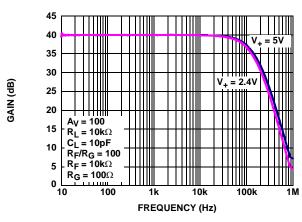


FIGURE 4. EL8172 FREQUENCY RESPONSE vs SUPPLY VOLTAGE

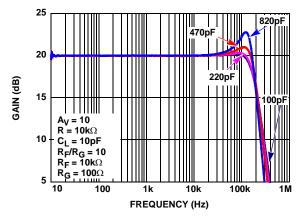


FIGURE 5. EL8171 FREQUENCY RESPONSE vs  $C_{\mbox{LOAD}}$ 

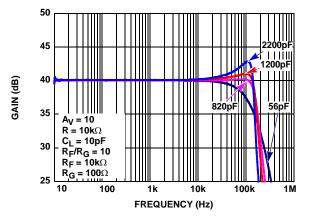


FIGURE 6. EL8172 FREQUENCY RESPONSE vs C<sub>LOAD</sub>

 $\textbf{\textit{Typical Performance Curves}} \ \ V_{+} = 5 \text{V}, \ V_{-} = 0 \text{V}, \\ V_{CM} = 2.5 \text{V}, \ V_{EN} = \text{V-}, \ R_{L} = \text{Open, unless otherwise specified.} \ \textbf{(Continued)}$ 

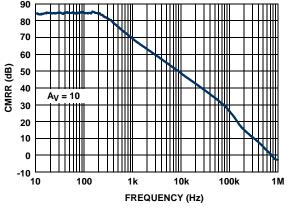


FIGURE 7. EL8171 CMRR vs FREQUENCY

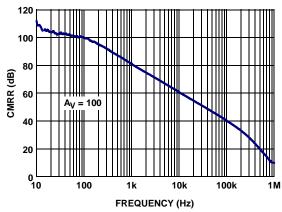


FIGURE 8. EL8172 CMRR vs FREQUENCY

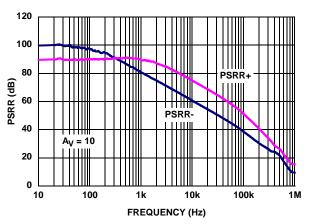


FIGURE 9. EL8171 PSRR vs FREQUENCY

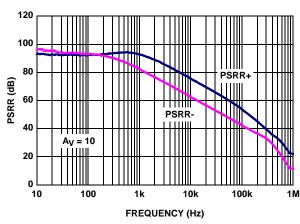


FIGURE 10. EL8172 PSRR vs FREQUENCY

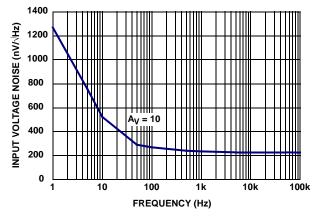


FIGURE 11. EL8171 VOLTAGE NOISE SPECTRAL DENSITY

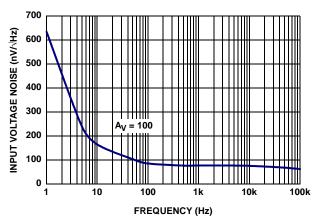


FIGURE 12. EL8172 VOLTAGE NOISE SPECTRAL DENSITY

# $\textbf{Typical Performance Curves} \ \, \text{V}_{+} = 5 \text{V}, \ \, \text{V}_{-} = 0 \text{V}, \\ \text{V}_{CM} = 2.5 \text{V}, \ \, \text{V}_{EN} = \text{V-}, \ \, \text{R}_{L} = \text{Open, unless otherwise specified.}$

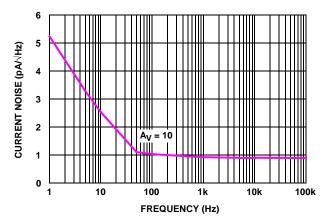


FIGURE 13. EL8171 CURRENT NOISE SPECTRAL DENSITY

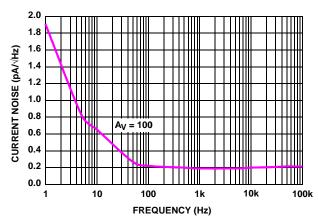


FIGURE 14. EL8172 CURRENT NOISE SPECTRAL DENSITY

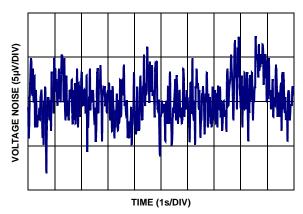


FIGURE 15. EL8171 0.1Hz TO 10Hz INPUT VOLTAGE NOISE (GAIN = 10)

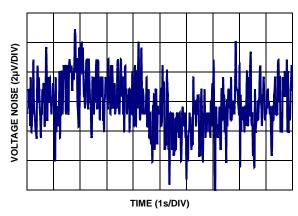


FIGURE 16. EL8172 0.1Hz TO 10Hz INPUT VOLTAGE NOISE (GAIN = 100)

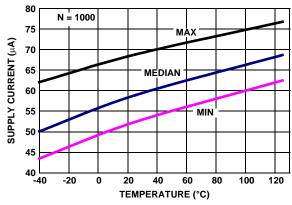


FIGURE 17. EL8171 SUPPLY CURRENT ENABLED vs TEMPERATURE,  $V_+$ ,  $V_- = \pm 2.5V$ ,  $V_{IN} = 0V$ 

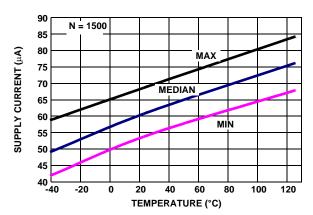


FIGURE 18. EL8172 SUPPLY CURRENT ENABLED vs TEMPERATURE,  $V_+, V_- = \pm 2.5V, V_{IN} = 0V$ 

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# $\textbf{\textit{Typical Performance Curves}} \ \ V_{+} = 5 \text{V}, \ V_{-} = 0 \text{V}, \\ V_{CM} = 2.5 \text{V}, \ V_{EN} = \text{V-}, \ R_{L} = \text{Open, unless otherwise specified.} \ \textbf{(Continued)}$

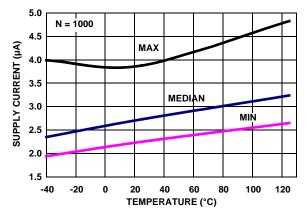


FIGURE 19. EL8171 SUPPLY CURRENT DISABLED vs TEMPERATURE,  $V_+$ ,  $V_- = \pm 2.5V$ ,  $V_{EN} = V_+$ ,  $V_{IN} = 0V$ 

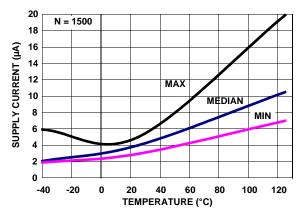


FIGURE 20. EL8172 SUPPLY CURRENT DISABLED vs TEMPERATURE,  $V_+$ ,  $V_- = \pm 2.5V$ ,  $V_{EN} = V_+$ ,  $V_{IN} = 0V$ 

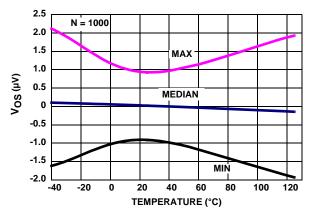


FIGURE 21. EL8171  $V_{OS}$  vs TEMPERATURE,  $V_+$ ,  $V_- = \pm 2.5V$ ,  $V_{IN} = 0V$ 

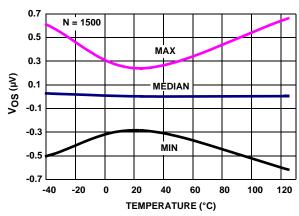


FIGURE 22. EL8172  $V_{OS}$  vs TEMPERATURE,  $V_+$ ,  $V_- = \pm 2.5V$ ,  $V_{IN} = 0V$ 

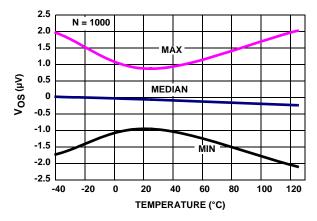


FIGURE 23. EL8171  $V_{OS}$  vs TEMPERATURE,  $V_+$ ,  $V_-$  = ±1.2V,  $V_{IN}$  = 0V

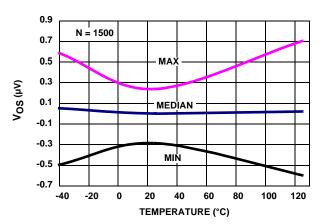


FIGURE 24. EL8172  $V_{OS}$  vs TEMPERATURE,  $V_+$ ,  $V_-$  = ±1.2V,  $V_{IN}$  = 0V

# $\textbf{Typical Performance Curves} \ \ V_{+} = 5 \ V, \ V_{-} = 0 \ V, V_{CM} = 2.5 \ V, \ V_{EN} = V -, \ R_{L} = Open, \ unless \ otherwise \ specified. \ \textbf{(Continued)}$

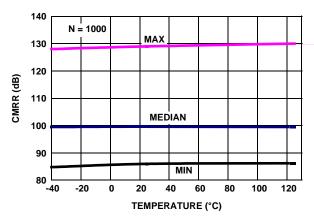


FIGURE 25. EL8171 CMRR vs TEMPERATURE,  $V_{CM} = +2.5V \text{ TO } -2.5V, V_+, V_- = \pm 2.5V$ 

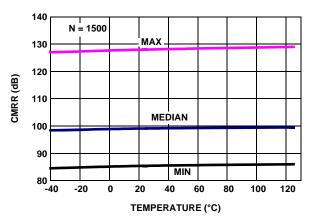


FIGURE 26. EL8172 CMRR vs TEMPERATURE,  $V_{CM} = +2.5V \text{ TO } -2.5V, V_{+}, V_{-} = \pm 2.5V$ 

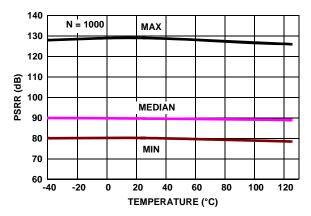


FIGURE 27. EL8171 PSRR vs TEMPERATURE,  $V_+$ ,  $V_- = \pm 1.2V$  TO  $\pm 2.5V$ 

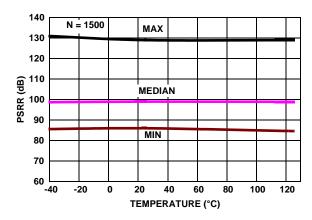


FIGURE 28. EL8172 PSRR vs TEMPERATURE,  $V_+$ ,  $V_-$  = ±1.2V TO ±2.5V

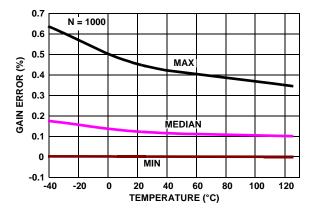


FIGURE 29. EL8171% GAIN ERROR vs TEMPERATURE,  $R_L = 100k$ 

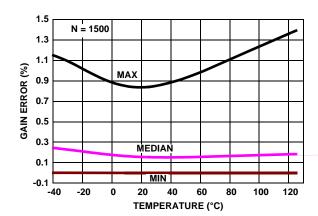


FIGURE 30. EL8172% GAIN ERROR vs TEMPERATURE,  $R_L = 100k \label{eq:RL}$ 

# $\textbf{Typical Performance Curves} \ \ V_{+} = 5 \ V, \ V_{-} = 0 \ V, \ V_{CM} = 2.5 \ V, \ V_{EN} = V -, \ R_{L} = Open, \ unless \ otherwise \ specified. \ \textbf{(Continued)}$

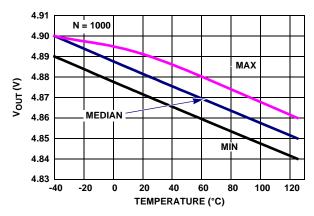


FIGURE 31. EL8171  $V_{OUT}$  HIGH vs TEMPERATURE,  $R_L = 1k$ ,  $V_+$ ,  $V_- = \pm 2.5V$ 

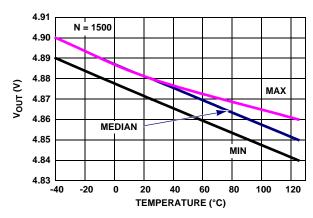


FIGURE 32. EL8172  $V_{OUT}$  HIGH vs TEMPERATURE,  $R_L = 1k$ ,  $V_+$ ,  $V_- = \pm 2.5V$ 

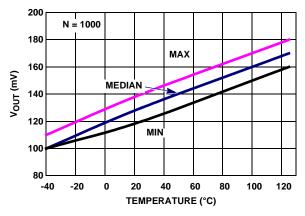


FIGURE 33. EL8171  $V_{OUT}$  LOW vs TEMPERATURE,  $R_L$  = 1k,  $V_+$ ,  $V_-$  = ±2.5V

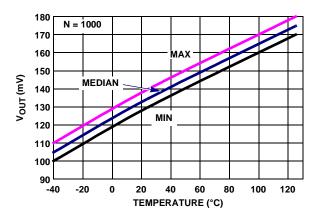


FIGURE 34. EL8172  $V_{OUT}$  LOW vs TEMPERATURE,  $R_L$  = 1k,  $V_+$ ,  $V_-$  = ±2.5V

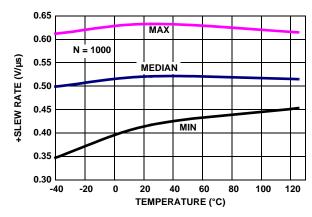


FIGURE 35. EL8171 +SLEW RATE vs TEMPERATURE,  $INPUT = \pm 0.015V @ GAIN + 100$ 

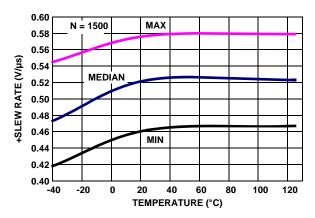


FIGURE 36. EL8172 + SLEW RATE vs TEMPERATURE, INPUT = ±0.015V @ GAIN + 100

# $\textbf{\textit{Typical Performance Curves}} \ \ V_{+} = 5 \text{V}, \ V_{-} = 0 \text{V}, \\ V_{CM} = 2.5 \text{V}, \ V_{EN} = \text{V-}, \ R_{L} = \text{Open, unless otherwise specified.} \ \textbf{(Continued)}$

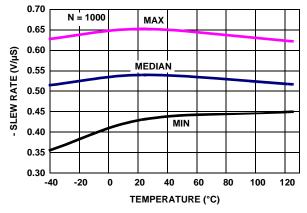


FIGURE 37. EL8171 -SLEW RATE vs TEMPERATURE, INPUT =  $\pm 0.015$ V @ GAIN + 100

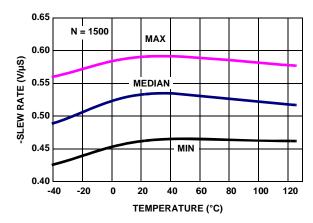
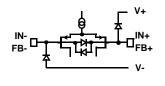


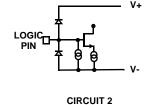
FIGURE 38. EL8172 -SLEW RATE vs TEMPERATURE, INPUT =  $\pm 0.015V$  @ GAIN + 100

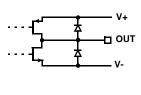
# Pin Descriptions

EL8171/EL8172	PIN NAME	EQUIVALENT CIRCUIT	PIN FUNCTION
1	ĒN	Circuit 2	Active LOW logic pins. When pulled above 2V, the corresponding channel turns off and OUT is high impedance. A channel is enabled when pulled below 0.8V. Built in pull downs define each $\overline{\text{EN}}$ pin LOW when left floating.
2	IN-	Circuit 1A, Circuit 1B	High impedance input terminals. EL8172 input circuit is shown in Circuit 1A, and
3	IN+	Circuit 1A, Circuit 1B	the EL8171 input circuit is shown in Circuit 1B. EL8171: to avoid offset drift, it is recommended that the terminals are not overdriven beyond 1V and the input current must never exceed 5mA.
4	V-	Circuit 4	Negative supply terminal.
5	FB-	Circuit 1A, Circuit 1B	High impedance feedback terminals. EL8172 input circuit is shown in Circuit 1A,
8	FB+	Circuit 1A, Circuit 1B	and the EL8171 input circuit is shown in Circuit 1B. EL8171: to avoid offset drift, it is recommended that the terminals are not overdriven beyond 1V and the input current must never exceed 5mA.
7	V+	Circuit 4	Positive supply terminal.
6	VOUT	Circuit 3	Output Voltage.

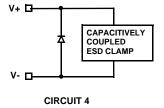


**CIRCUIT 1A** 





**CIRCUIT 3** 



FB- V-

**CIRCUIT 1B** 

# Description of Operation and Application Information

## **Product Description**

The EL8171 and EL8172 are micropower instrumentation amplifiers (in-amps) which deliver rail-to-rail input amplification and rail-to-rail output swing on a single 2.4V to 5.5V supply. The EL8171 and EL8172 also deliver excellent DC and AC specifications while consuming only 65 $\mu$ A typical supply current. Because EL8171 and EL8172 provide an independent pair of feedback terminals to set the gain and to adjust the output level, these in-amps achieve high common-mode rejection ratio regardless of the tolerance of the gain setting resistors. The EL8171 is internally compensated for a minimum closed loop gain of 10 or greater, well suited for moderate to high gains. For higher gains, the EL8172 is internally compensated for a minimum gain of 100. An  $\overline{\text{EN}}$  pin is used to reduce power consumption, typically 4.5 $\mu$ A, while the instrumentation amplifier is disabled.

## Input Protection

All input and feedback terminals of the EL8171 and EL8172 have internal ESD protection diodes to both positive and negative supply rails, limiting the input voltage to within one diode drop beyond the supply rails. The inverting inputs and FB- inputs have ESD diodes to the V-rail, and the non-inverting inputs and FB+ terminals have ESD diodes to the V+ rail. The EL8172 has additional back-to-back diodes across the input terminals and also across the feedback terminals. If overdriving the inputs is necessary, the external input current must never exceed 5mA. On the other hand, the EL8171 has no clamps to limit the differential voltage on the input terminals allowing higher differential input voltages at lower gain applications. It is recommended however, that the input terminals of the EL8171 are not overdriven beyond 1V to avoid offset drift. An external series resistor may be used as an external protection to limit excessive external voltage and current from damaging the inputs.

# Input Stage and Input Voltage Range

The input terminals (IN+ and IN-) of the EL8171 and EL8172 are single differential pair P-MOSFET devices aided by an Input Range Enhancement Circuit (IREC) to increase the headroom of operation of the common-mode input voltage. The feedback terminals (FB+ and FB-) also have a similar topology. As a result, the input common-mode voltage range of both the EL8171 and EL8172 is rail-to-rail. These in-amps are able to handle input voltages that are at or slightly beyond the supply and ground making these in-amps well suited for single 5V or 3.3V low voltage supply systems. There is no need to move the common-mode input of the in-amps to achieve symmetrical input voltage.

11

### Output Stage and Output Voltage Range

A pair of complementary MOSFET devices drive the output  $V_{OUT}$  to within a few mV of the supply rails. At a  $100k\Omega$  load, the PMOS sources current and pulls the output up to 4mV below the positive supply, while the NMOS sinks current and pulls the output down to 4mV above the negative supply, or ground in the case of a single supply operation. The current sinking and sourcing capability of the EL8171 and EL8172 are internally limited to less than 35mA.

### Gain Setting

 $V_{IN},$  the potential difference across IN+ and IN-, is replicated (less the input offset voltage) across FB+ and FB-. The obsession of the EL8171 and EL8172 in-amp is to maintain the differential voltage across FB+ and FB- equal to IN+ and IN-; (FB+ - FB-) = (IN+ - IN-). Consequently, the transfer function can be derived. The gain of the EL8171 and EL8172 is set by two external resistors, the feedback resistor  $R_{\rm F},$  and the gain resistor  $R_{\rm G}$ .

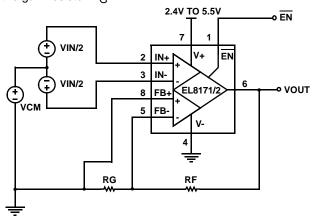


FIGURE 39. CIRCUIT 1 - GAIN IS BY EXTERNAL RESISTORS

RE AND Re

$$V_{OUT} = \left(1 + \frac{R_F}{R_G}\right) V_{IN} \tag{EQ. 1}$$

In Figure 39, the FB+ pin and one end of resistor RG are connected to GND. With this configuration, Equation 1 is only true for a positive swing in  $V_{IN}$ ; negative input swings will be ignored and the output will be at ground.

## Reference Connection

Unlike a three-op amp instrumentation amplifier, a finite series resistance seen at the REF terminal does not degrade the EL8171 and EL8172's high CMRR performance, eliminating the need for an additional external buffer amplifier. Circuit 2 (Figure 40) uses the FB+ pin to provide a high impedance REF terminal.

intersil FN6293.3 August 3, 2007

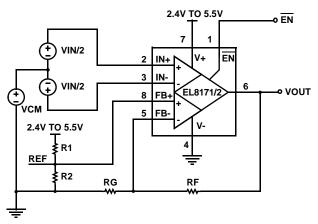


FIGURE 40. CIRCUIT 2 - GAIN SETTING AND REFERENCE CONNECTION

$$V_{OUT} = \left(1 + \frac{R_F}{R_G}\right)(V_{IN}) + \left(1 + \frac{R_F}{R_G}\right)(V_{REF})$$
 (EQ. 2)

The FB+ pin is used as a REF terminal to center or to adjust the output. Because the FB+ pin is a high impedance input, an economical resistor divider can be used to set the voltage at the REF terminal without degrading or affecting the CMRR performance. Any voltage applied to the REF terminal will shift  $V_{OUT}$  by  $V_{REF}$  times the closed loop gain, which is set by resistors  $R_{\text{F}}$  and  $R_{\text{G}}$ . See Circuit 2 (Figure 40). Note that any noise or unwanted signals on the reference supply will be amplified at the output according to Equation 2.

The FB+ pin can also be connected to the other end of resistor,  $R_G$ . See Circuit 3 (Figure 41). Keeping the basic concept that the EL8171 and EL8172 in-amps maintain constant differential voltage across the input terminals and feedback terminals (IN+ - IN- = FB+ - FB-), the transfer function of Circuit 3 can be derived. Note that the VREF gain term is eliminated and susceptibility to external noise is reduced, however the VREF source must be capable of sourcing or sinking the feedback current from  $V_{\mbox{\scriptsize OUT}}$  through  $R_{\mbox{\scriptsize F}}$  and  $R_{\mbox{\scriptsize G}}$ .

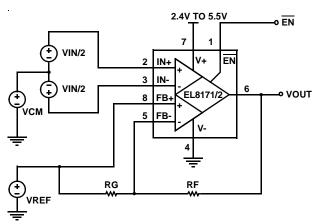


FIGURE 41. CIRCUIT 3 - REFERENCE CONNECTION WITH AN AVAILABLE VREF

$$V_{OUT} = \left(1 + \frac{R_F}{R_G}\right)(V_{IN}) + (V_{REF})$$
 (EQ. 3)

#### External Resistor Mismatches

Because of the independent pair of feedback terminals provided by the EL8171 and EL8172, the CMRR is not degraded by any resistor mismatches. Hence, unlike a three op amp and especially a two op amp in-amp, the EL8171 and EL8172 reduce the cost of external components by allowing the use of 1% or more tolerance resistors without sacrificing CMRR performance. The EL8171 and EL8172 CMRR will be maintained regardless of the tolerance of the resistors used.

# Gain Error and Accuracy

The EL8172 has a Gain Error (EG) of 0.2% typical. The EL8171 has an EG of 0.15% typical. The gain error indicated in the "Electrical Specifications" table on page 2 is the inherent gain error of the EL8171 and EL8172 and does not include the gain error contributed by the resistors. There is an additional gain error due to the tolerance of the resistors used. The resulting non-ideal transfer function effectively becomes:

$$V_{OUT} = \left(1 + \frac{R_F}{R_G}\right) \times [1 - (E_{RG} + E_{RF} + E_G)] \times V_{IN}$$
 (EQ. 4)

Where:

E<sub>RG</sub> = Tolerance of R<sub>G</sub>

ERF = Tolerance of RF

 $E_G$  = Gain Error of the EL8171 or EL8172

The term  $[1-(E_{RG} + E_{RF} + E_{G})]$  is the deviation from the theoretical gain. Thus,  $(E_{RG} + E_{RF} + E_{G})$  is the total gain error. For example, if 1% resistors are used for the EL8171, the total gain error would be:

$$= \pm (E_{RG} + E_{RF} + E_{G}(typical))$$

$$= \pm (0.01 + 0.01 + 0.003)$$

$$= \pm 2.3\%$$
(EQ. 5)

### Disable/Power-Down

The EL8171 and EL8172 can be powered down reducing the supply current to typically 4.5 $\mu$ A. When disabled, the output is in a high impedance state. The active low  $\overline{\text{EN}}$  bar pin has an internal pull-down and hence can be left floating and the in-amp enabled by default. When the  $\overline{\text{EN}}$  bar is connected to an external logic, the in-amp will power down when  $\overline{\text{EN}}$  bar is pulled above 2V, and will power on when  $\overline{\text{EN}}$  bar is pulled below 0.8V.

## **Power Dissipation**

It is possible to exceed the +150°C maximum junction temperatures under certain load and power-supply conditions. It is therefore important to calculate the maximum junction temperature (T<sub>JMAX</sub>) for all applications to determine if power supply voltages, load conditions, or package type need to be modified to remain in the safe operating area. These parameters are related in Equation 6:

$$T_{JMAX} = T_{MAX} + (\theta_{JA} x PD_{MAXTOTAL})$$
 (EQ. 6)

#### where:

- P<sub>DMAXTOTAL</sub> is the sum of the maximum power dissipation of each amplifier in the package (PD<sub>MAX</sub>)
- PD<sub>MAX</sub> for each amplifier can be calculated as shown in Equation 7:

$$PD_{MAX} = 2*V_{S} \times I_{SMAX} + (V_{S} - V_{OUTMAX}) \times \frac{V_{OUTMAX}}{R_{L}}$$
(EQ. 7)

#### where:

- T<sub>MAX</sub> = Maximum ambient temperature
- $\theta_{JA}$  = Thermal resistance of the package
- PD<sub>MAX</sub> = Maximum power dissipation of 1 amplifier
- V<sub>S</sub> = Supply voltage (Magnitude of V<sub>+</sub> and V<sub>-</sub>)
- I<sub>MAX</sub> = Maximum supply current of 1 amplifier
- V<sub>OUTMAX</sub> = Maximum output voltage swing of the application
- R<sub>I</sub> = Load resistance

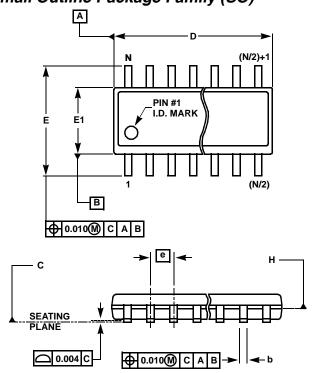
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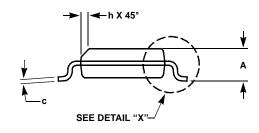
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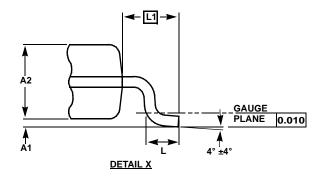
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# Small Outline Package Family (SO)







# **MDP0027**

# **SMALL OUTLINE PACKAGE FAMILY (SO)**

	INCHES								
SYMBOL	SO-8	SO-14	SO16 (0.150")	SO16 (0.300") (SOL-16)	SO20 (SOL-20)	SO24 (SOL-24)	SO28 (SOL-28)	TOLERANCE	NOTES
Α	0.068	0.068	0.068	0.104	0.104	0.104	0.104	MAX	-
A1	0.006	0.006	0.006	0.007	0.007	0.007	0.007	±0.003	-
A2	0.057	0.057	0.057	0.092	0.092	0.092	0.092	±0.002	-
b	0.017	0.017	0.017	0.017	0.017	0.017	0.017	±0.003	-
С	0.009	0.009	0.009	0.011	0.011	0.011	0.011	±0.001	-
D	0.193	0.341	0.390	0.406	0.504	0.606	0.704	±0.004	1, 3
Е	0.236	0.236	0.236	0.406	0.406	0.406	0.406	±0.008	-
E1	0.154	0.154	0.154	0.295	0.295	0.295	0.295	±0.004	2, 3
е	0.050	0.050	0.050	0.050	0.050	0.050	0.050	Basic	-
L	0.025	0.025	0.025	0.030	0.030	0.030	0.030	±0.009	-
L1	0.041	0.041	0.041	0.056	0.056	0.056	0.056	Basic	-
h	0.013	0.013	0.013	0.020	0.020	0.020	0.020	Reference	-
N	8	14	16	16	20	24	28	Reference	-

NOTES

Rev. M 2/07

- 1. Plastic or metal protrusions of 0.006" maximum per side are not included.
- 2. Plastic interlead protrusions of 0.010" maximum per side are not included.
- 3. Dimensions "D" and "E1" are measured at Datum Plane "H".
- 4. Dimensioning and tolerancing per ASME Y14.5M-1994